

Patent title:	Radiation detection element, radiation detector and radiation
	detection apparatus
FBK center:	СММ
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Application(s):	Radiation detection
Keyword(s):	Radiation detection apparatus
Abstract:	A radiation detection element comprises: a semiconductor part
	generating an electric charge by entrance of radiation; a signal
	output electrode provided at the semiconductor part and outputting
	a signal caused by the electric charge; a potential gradient
	generation electrode provided at the semiconductor part, for
	applying voltage such that a potential gradient in which a potential
	varies toward the signal output electrode is generated inside the
	semiconductor part; a collection electrode provided at the
	semiconductor part, for collecting electric charges not derived from
	radiation; an insulating film provided on a side of the
	semiconductor part where the signal output electrode is located;
	and a conductive layer provided between the insulating film and a
	part of the semiconductor part, and having electric resistance lower than the electric resistance of the semiconductor part and higher
	than the electric resistance of the semiconductor part and higher than the electric resistance of the collection electrode. The
	conductive layer is located at a position where a distance from the
	signal output electrode is equal to or longer than a distance
	between the collection electrode and the signal output electrode.

